

NOT RECOMMENDED FOR NEW DESIGN CONTACT US



DMN61D9U

N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
60V	2Ω @ V _{GS} = 5V	380mA
	2.5Ω @ V _{GS} = 2.5V	340mA

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor controls
- Power management functions
- Backlighting

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- · Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Up To 2kV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

https://www.diodes.com/products/automotive/automotive-products/.

 This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.

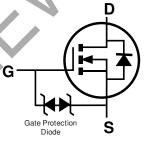
https://www.diodes.com/quality/product-definitions/

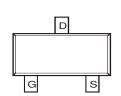
Mechanical Data

- Package: SOT23
- Package Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Alloy 42
 Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.008 grams (Approximate)









Top View

Equivalent Circuit

Top View

Ordering Information (Note 4)

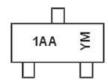
Part Number	Dookogo	Packing	
Part Number	Package	Qty.	Carrier
DMN61D9U-7	SOT23	3000	Tape & Reel
DMN61D9U-13	SOT23	10000	Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information



1AA = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: J = 2022) M = Month (ex: 9 = September)

Date Code Key

Year	2015		2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	С		J	K	L	М	N	0	Р	R	S	Т
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Maximum Ratings $(@T_A = +25^{\circ}C, unless otherwise specified.)$

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	60	V
Gate-Source Voltage			Vgss	±20	V
Continuous Drain Current (Note C) Vos. F.O.V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	lo	380 300	mA
Continuous Drain Current (Note 6) V _{GS} = 5.0V	t<5s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	lp	430 340	mA
Maximum Continuous Body Diode Forward Current (Note 6)			Is	0.4	А
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%	6) (Note 6		IDM	1.2	A

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Total Power Dissipation (Note 5)		P_{D}	370	mW	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Reja	351	°C/W	
mermai nesistance, Junction to Ambient (Note 5)	t<5s	МӨЈА	292	C/VV	
Total Power Dissipation (Note 6)		P_{D}	540	mW	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Davi	221	°C/W	
mermal resistance, sunction to Ambient (Note o)	t<5s	Reja	197	O/VV	
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	ô	

5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.



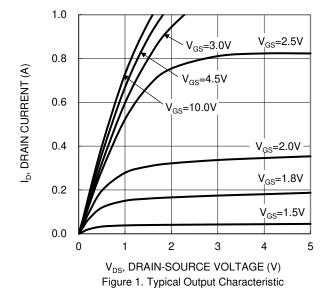
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

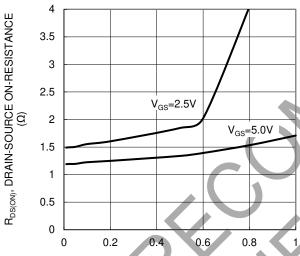
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)		•			•	
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current	IDSS	_	_	1.0	μΑ	$V_{DS} = 60V$, $V_{GS} = 0V$
Gate-Source Leakage	Igss	_	_	±10	μΑ	$V_{GS} = \pm 20V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	0.5	_	1.0	V	$V_{DS} = 10V, I_D = 250\mu A$
			1.2	2.0		$V_{GS} = 5.0V, I_D = 0.05A$
Static Drain-Source On-Resistance	RDS(ON)	_	1.6	2.5	Ω	$V_{GS} = 2.5V, I_D = 0.05A$
			2.5	3.5		$V_{GS} = 1.8V, I_D = 0.05A$
Forward Transconductance	Y _{fs}	200	_	_	mS	$V_{DS} = 10V, I_{D} = 0.2A$
Diode Forward Voltage	VsD	_	0.75	1.4	V	$V_{GS} = 0V, I_S = 115mA$
DYNAMIC CHARACTERISTICS (Note 8)	•	•	•			
Input Capacitance	Ciss	_	28.5	_	pF	V 20V V 0V
Output Capacitance	Coss	_	3.9	_	pF	V _{DS} = 30V, V _{GS} = 0V f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	2.5	1	pF	1 = 1.0W112
Gate Resistance	Rg	_	65		Ω	f = 1MHz , V _{GS} = 0V, V _{DS} = 0V
Total Gate Charge	Qg	_	0.4	1	nC	V 45V V 40V
Gate-Source Charge	Qgs		0.1	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$
Gate-Drain Charge	Q _{gd}		0.1		nC	Ip = 250mA
Turn-On Delay Time	tD(ON)	-	2.1	/ -	ns	
Turn-On Rise Time	tR	17	1.8		ns	V _{DD} = 30V, V _{GS} = 10V,
Turn-Off Delay Time	t _D (OFF)	+7	14.4		ns	$R_G = 25\Omega$, $I_D = 200mA$
Turn-Off Fall Time	tr	7	8.4		ns	Ť

Notes:

- 7. Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to product testing.







I_D, DRAIN-SOURCE CURRENT (A) Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

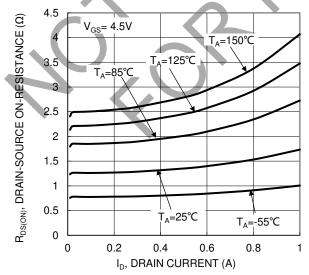
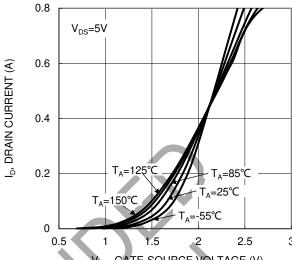


Figure 5. Typical On-Resistance vs. Drain Current and Temperature



V_{GS}, GATE-SOURCE VOLTAGE (V) Figure 2. Typical Transfer Characteristic

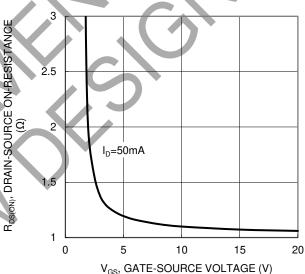


Figure 4. Typical Transfer Characteristic

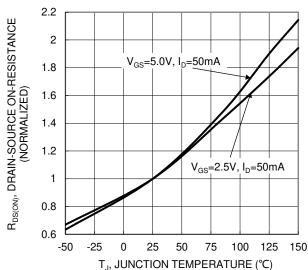


Figure 6. On-Resistance Variation with Junction Temperature



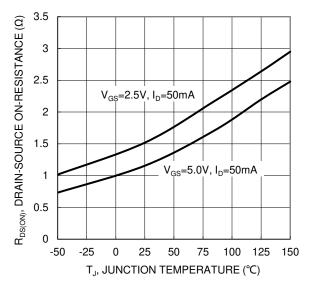


Figure 7. On-Resistance Variation with Junction Temperature

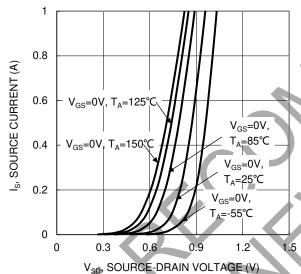


Figure 9. Diode Forward Voltage vs. Current

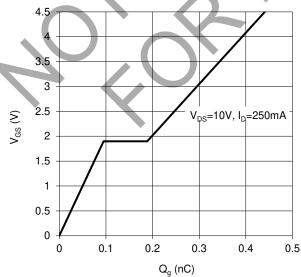


Figure 11. Gate Charge

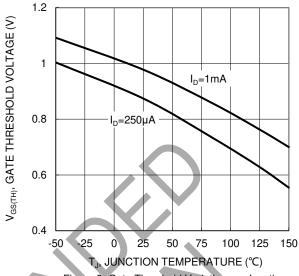
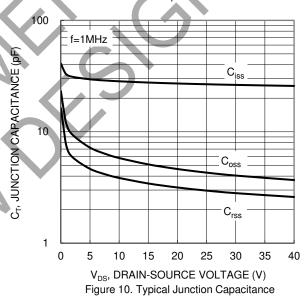


Figure 8. Gate Threshold Variation vs. Junction Temperature



10 $R_{\text{DS}(\text{ON})}$ Limited DRAIN CURRENT (A) 1 0.1 =10ms $T_{J(MAX)}$ =150°C <u>ث</u> 0.01 –10s Single Pulse DUT on 1*MRP board $V_{GS}=5V$ 0.001 0.1 100 V_{DS}, DRAIN-SOURCE VOLTAGE (V)

Figure 12. SOA, Safe Operation Area



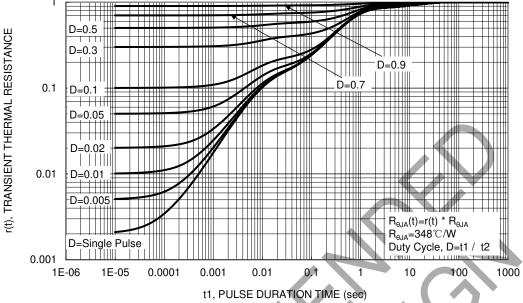


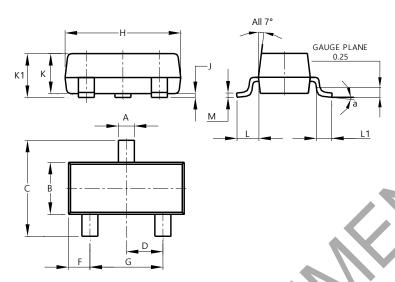
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

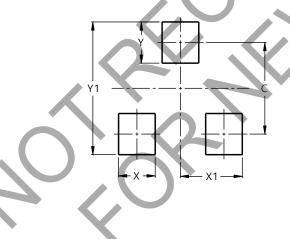


SOT23								
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
O	2.30	2.50	2.40					
Р	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Ξ	2.80	3.00	2.90					
7	0.013	0.10	0.05					
K	0.890	1.00	0.975					
K1	0.903	1.10	1.025					
٦	0.45	0.61	0.55					
L1	0.25	0.55	0.40					
Μ	0.085	0.150	0.110					
a	0°	8°						
AII	All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Υ	0.9
Y1	2.9



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